



گروه فنی مهندسی جوش و برش مقدم

اعتماد از شما کیفیت و تخصص از ما

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مشهد خیام شمالی 63 خیابان پردیس 3

برای کسب اطلاعات بیشتر بر روی لینک ها کلیک کنید

- 7 سال سابقه آموزش تعمیرات تخصصی دستگاه های جوش اینورتری تک فاز و 3 فاز
- 7 سال سابقه فروش قطعات الکترونیکی دستگاه جوش تک فاز و 3 فاز
- آموزش تخصصی تحلیل دستگاه های جوش اینورتری مختص ابراز فروشان
- آموزش تخصصی ابراز آلات شارژی

TLP250(INV)

TRANSISTOR INVERTER
INVERTERS FOR AIR CONDITIONER
IGBT GATE DRIVE
POWER MOS FET GATE DRIVE

The TOSHIBA TLP250(INV) consists of a GaAlAs light emitting diode and a integrated photodetector.

This unit is 8-lead DIP.

TLP250(INV) is suitable for gate driving circuit of IGBT or power MOS FET.

- Input Threshold Current : $I_F = 5\text{mA}(\text{MAX})$
- Supply Current(I_{CC}) : $11\text{mA}(\text{MAX})$
- Supply Voltage(V_{CC}) : $10\sim 35\text{V}$
- Output Current(I_O) : $\pm 2.0\text{A}(\text{MAX})$
- Switching Time(t_{PLH}/t_{PHL}) : $0.5\mu\text{s}(\text{MAX})$
- Isolation Voltage : 2500VRms
- UL Recognized : UL1577, File No.E67349
- Option(D4)

VDE Approved : DIN VDE0884/06.92 Certificate No.76823

Maximum Operating Insulation Voltage : 630V_{PK}

Highest Permissible Over Voltage : 4000V_{PK}

(Note):When a VDE0884 approved type is needed,

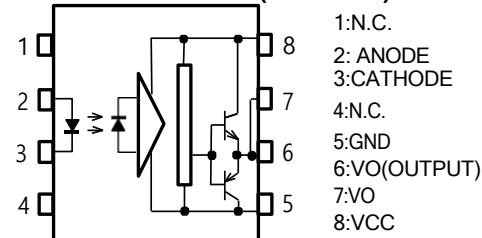
Please designate the "Option(D4)"

- Creepage Distance : $6.4\text{mm}(\text{MIN})$
- Clearance : $6.4\text{mm}(\text{MIN})$

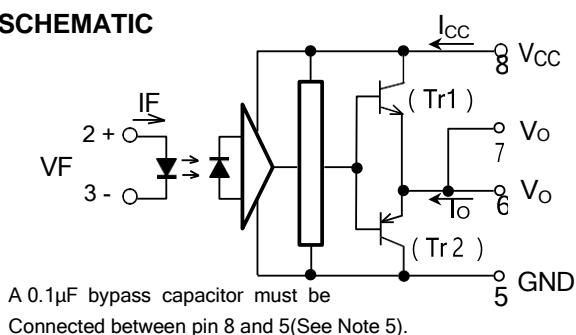
TRUTH TABLE

		Tr 1	Tr 2
INPUT LED	ON	ON	OFF
	OFF	OFF	ON

PIN CONFIGURATION(TOP VIEW)



SCHEMATIC



MAXIMUM RATINGS ($T_a=25^\circ\text{C}$)

CHARACTERISTIC			SYMBOL	RATING	UNIT		
LED	Forward Current		I_F	20	mA		
	Forward Current Derating ($T_a \geq 70^\circ\text{C}$)		$\Delta I_F / \Delta T_a$	-0.36	mA / $^\circ\text{C}$		
	Peak Transient Forward Current (Note 1)		I_{FPT}	1	A		
	Reverse Voltage		V_R	5	V		
	Junction Temperature		T_j	125	$^\circ\text{C}$		
DETECTOR	"H" Peak Output Current	PW $\leq 2.5\mu\text{s}$, f $\leq 15\text{ kHz}$	I_{OPH}	-1.5	A		
		PW $\leq 1.0\mu\text{s}$, f $\leq 15\text{ kHz}$		-2.0			
	"L" Peak Output Current	PW $\leq 2.5\mu\text{s}$, f $\leq 15\text{ kHz}$	I_{OPL}	+1.5	A		
		PW $\leq 1.0\mu\text{s}$, f $\leq 15\text{ kHz}$		+2.0			
	Output Voltage	($T_a \leq 70^\circ\text{C}$)	V_o	35	V		
		($T_a = 85^\circ\text{C}$)		24			
	Supply Voltage	($T_a \leq 70^\circ\text{C}$)	V_{CC}	35	V		
		($T_a = 85^\circ\text{C}$)		24			
	Output Voltage Derating ($T_a \geq 70^\circ\text{C}$)		$\Delta V_o / \Delta T_a$	-0.73	V / $^\circ\text{C}$		
	Supply Voltage Derating ($T_a \geq 70^\circ\text{C}$)		$\Delta V_{CC} / \Delta T_a$	-0.73	V / $^\circ\text{C}$		
Junction Temperature			T_j	125	$^\circ\text{C}$		
Operating Frequency (Note 3)			f	25	kHz		
Operating Temperature Range			T_{opr}	-20~85	$^\circ\text{C}$		
Storage Temperature Range			T_{stg}	-55~125	$^\circ\text{C}$		
Lead Soldering Temperature(10s)			T_{sol}	260	$^\circ\text{C}$		
Isolation Voltage (AC,1min., R.H. $\leq 60\%$, $T_a = 25^\circ\text{C}$) (Note 4)			BV_s	2500	Vrms		

(Note 1) : Pulse width PW $\leq 1\mu\text{s}$, 300pps

(Note 2) : Exponential Waveform

(Note 3) : Exponential Waveform $I_{OPH} \leq -1.0\text{A}$ ($\leq 2.5\mu\text{s}$), $I_{OPL} \leq +1.0\text{A}$ ($\leq 2.5\mu\text{s}$)

(Note 4) : Device considerd a two terminal device : pins 1,2,3 and 4 shorted together and pins 5,6,7 and 8 shorted together.

(Note 5) : A ceramic capacitor($0.1\mu\text{F}$) should be connected from pin 8 to pin 5 to stabilize the operation of the high gain linear amplifier. Failure to provide the bypassing may impair the switching property. The total lead length between capacitor and coupler should not exceed 1cm.

RECOMMENDED OPERATING CONDITIONS

CHARACTERISTIC	SYMBOL	MIN	TYP.	MAX	UNIT
Input Current, ON	$I_{F(ON)}$	7	8	10	mA
Input Voltage, OFF	$V_{F(OFF)}$	0	—	0.8	V
Supply Voltage	V_{CC}	15	—	30	V
Peak Output Current	I_{OPH} / I_{OPL}	—	—	± 0.5	A
Operating Temperature	T_{opr}	-20	25	70	$^\circ\text{C}$

ELECTRICAL CHARACTERISTICS (Ta = -20~70°C, Unless otherwise specified)

CHARACTERISTIC		SYMBOL	TEST CIRCUIT	TEST CONDITION		MIN	TYP.	MAX	UNIT
Input Forward Voltage		V _F	—	I _F = 10 mA, Ta = 25°C		—	1.6	1.8	V
Temperature Coefficient of Forward Voltage		ΔV _F /ΔTa	—	I _F = 10 mA		—	-2.0	—	mV /°C
Input Reverse Current		I _R	—	V _R = 5 V, Ta = 25°C		—	—	10	μA
Input Capacitance		C _T	—	V = 0, f = 1 MHz, Ta = 25°C		—	45	250	pF
Output Current	"H" Level	I _{OPH}	2	V _{CC} = 30 V (*)1)	I _F = 10 mA V ₈₋₆ = 4 V	-1.0	-1.5	—	A
	"L" Level	I _{OPL}	1		I _F = 0 V ₆₋₅ = 2.5 V	1.0	2	—	
Output Voltage	"H" Level	V _{OH}	3	V _{CC1} = +15 V V _{EE1} = -15 V R _L = 200Ω, I _F = 5 mA		11	12.8	—	V
	"L" Level	V _{OL}	4	V _{CC1} = +15 V V _{EE1} = -15 V R _L = 200Ω, V _F = 0.8 V		—	-14.2	-12.5	
Supply Current	"H" Level	I _{CCH}	—	V _{CC} = 30 V	I _F = 10 mA Ta = 25°C	—	7	—	mA
	"L" Level	I _{CCL}	—		I _F = 10 mA	—	—	11	
	"H" Level	I _{CCH}	—		I _F = 0 mA Ta = 25°C	—	7.5	—	mA
	"L" Level	I _{CCL}	—		I _F = 0 mA	—	—	11	
Threshold Input Current	L→H	I _{FLH}	—	V _{CC1} = +15 V V _{EE1} = -15 V R _L = 200Ω, V _O > 0V		—	1.2	5	mA
Threshold Input Voltage	H→L	V _{FHL}	—	V _{CC1} = +15 V V _{EE1} = -15 V R _L = 200Ω, V _O < 0V		0.8	—	—	V
Supply Voltage		V _{CC}	—	—		10	—	35	V
Capacitance (Input-Output)		C _S	—	V _S = 0, f = 1 MHz, Ta = 25°C		—	1.0	2.0	pF
Resistance (Input-Output)		R _S	—	V _S = 500 V, Ta = 25°C R.H.≤60%		1×10 ¹²	10 ¹⁴	—	Ω

(*) : All typical values are at Ta=25°C

(*1) : Duration of IO time ≤ 50μs

SWITCHING CHARACTERISTICS (Ta = -20~70°C, Unless otherwise specified)

CHARACTERISTIC		SYMBOL	TEST CIRCUIT	TEST CONDITION	MIN	TYP.	MAX	UNIT
Propagation	L→H	t_{PLH}	5	$I_F = 8 \text{ mA}$, $V_{CC} = 15 \text{ V}$ $R_L = 20\Omega$, $C_L = 10\text{nF}$	0.05	0.15	0.5	μs
Delay Time	H→L	t_{PHL}			0.05	0.15	0.5	
Switching Time Dispersion between ON and OFF		$ t_{PHL}-t_{PLH} $			—	—	0.45	
Output Rise Time		t_r			—	—	—	
Output Fall Time		t_f			—	—	—	
Common Mode Transient Immunity at High Level Output		CM_H	6	$V_{CM} = 1000 \text{ V}$, $I_F = 8 \text{ mA}$ $V_{CC} = 30 \text{ V}$, $T_a = 25^\circ\text{C}$	-15000	—	—	$\text{V}/\mu\text{s}$
Common Mode Transient Immunity at Low Level Output		CM_L		$V_{CM} = 1000 \text{ V}$, $I_F = 0 \text{ mA}$ $V_{CC} = 30 \text{ V}$, $T_a = 25^\circ\text{C}$	15000	—	—	$\text{V}/\mu\text{s}$

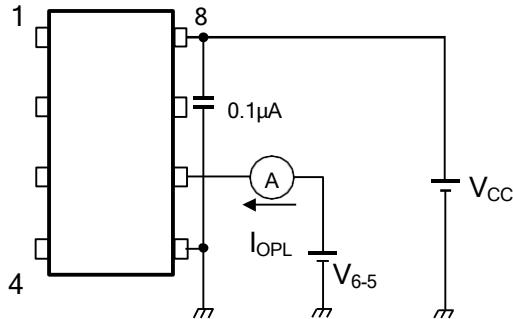
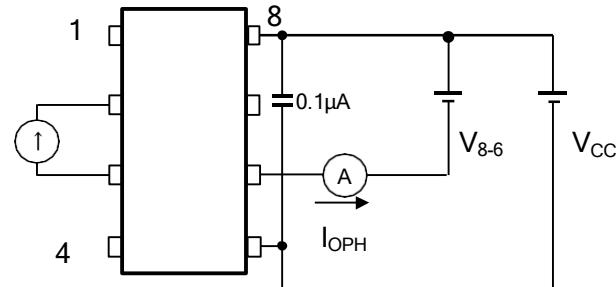
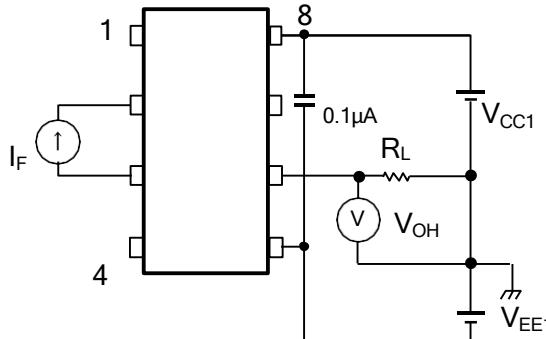
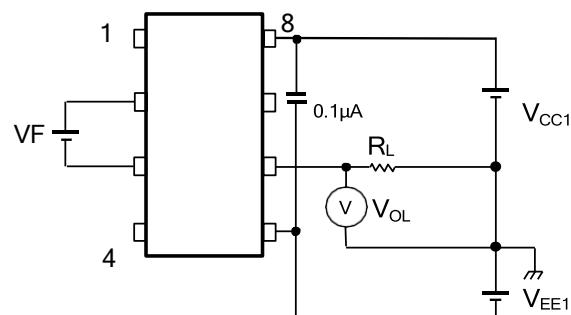
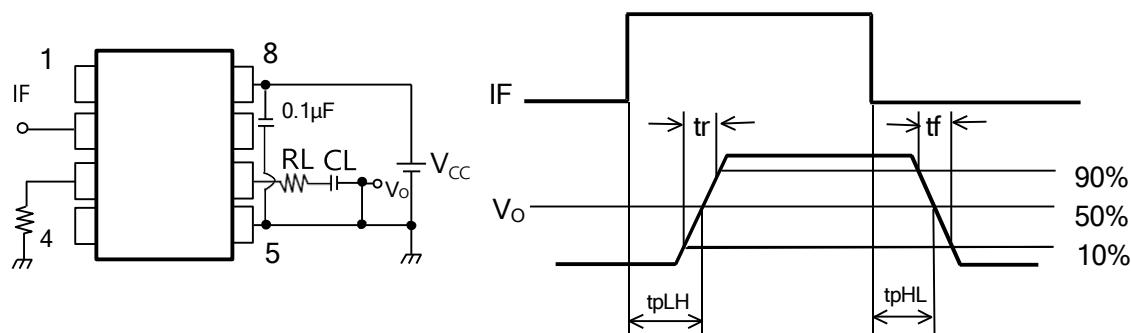
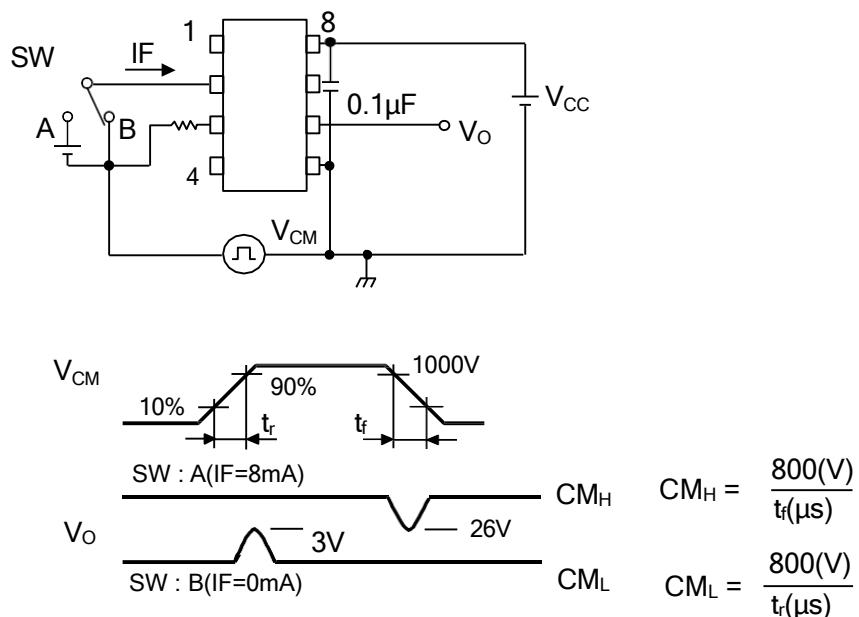
Fig.1 I_{OPL} TEST CIRCUITFig.2 I_{OPH} TEST CIRCUITFig.3 V_{OH} TEST CIRCUITFig.4 V_{OL} TEST CIRCUIT

Fig.5 tpLH、tpHL、tr、tf TEST CIRCUIT

Fig.6 CM_H, CM_L TEST CIRCUIT

CML(CMH) is the maximum rate of rise(fall) of the common mode voltage that can be sustained with the output voltage in the low(high)state.

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000707EBC

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